

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of forming a fine pattern, comprising the steps of:
forming a silicon-oxide-based film over a substrate by using ~~an oxidizing gas containing nitrogen~~ SiH₄ and N₂O as a material gas material gases at a reaction temperature of over 400 °C;
forming a chemically-amplified photoresist layer on the silicon-oxide-based film; and
transferring a mask pattern onto the chemically-amplified photoresist layer upon exposure through a mask,
wherein, in the step of forming the silicon-oxide-based film, a nitrogen content of a surface of the silicon-oxide-based film is made to about a value of 0.01 atm% to ~~0.1 atm%~~ 0.08 atm%.
2. (Canceled)
3. (Previously Presented) The method of forming a fine pattern according to claim 1, further comprising a step of exposing the surface of the silicon-oxide-based film to plasma atmosphere of O₂ or N₂O between the step of forming the silicon-oxide-based film and the step of forming the chemically-amplified photoresist layer.
4. (Canceled)
5. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:
forming a silicon-oxide-based film over an underlying layer, wherein the silicon-oxide-based film is formed by using ~~an oxidizing gas containing nitrogen~~ SiH₄ and N₂O as a material gas material gases at a reaction temperature of over 400 °C such that a surface of the silicon-oxide-based film has a nitrogen content of about 0.01 atm% to ~~0.1 atm%~~ 0.08 atm%;
forming a chemically-amplified photoresist layer on the silicon-oxide-based film;
transferring a mask pattern onto the chemically-amplified photoresist layer upon exposure through a mask; and
etching the underlying layer by way of a resist pattern, to thereby form a fine pattern in the underlying layer.

6. (Currently Amended) The method of forming a fine pattern according to claim 1, wherein the silicon-oxide-based film is deposited ~~at a temperature of 400°C or more~~ by means of a plasma CVD technique.

7. (Canceled).

8. (New) The method of forming a fine pattern according to claim 1, wherein the silicon-oxide-based film is formed at a reaction temperature of 450 °C or more.

9. (New) The method of forming a fine pattern according to claim 5, wherein the silicon-oxide-based film is formed at a reaction temperature of 450 °C or more.